

IN THE CLAIMS

1. (Currently amended) A method for forming ~~[[an]]~~a composite oxide layer having a first thickness in an integrated circuit device, the method comprising:

growing a thermal oxide layer having a second thickness thinner than the first thickness on a surface of a semiconductor substrate in a chemical vapor deposition (CVD) apparatus; and
forming a CVD oxide layer~~[[.]]~~directly on the thermal oxide layer in the CVD apparatus
after growing the thermal oxide layer, the CVD oxide layer having a third thickness substantially equal to a difference between the first thickness and the second thickness~~directly on the thermal oxide layer in the same CVD apparatus.~~

2. (Original) The method of claim 1, wherein the thermal oxide layer is formed to a thickness of approximately 20Å to 100Å.

3. (Previously presented) The method of claim 1, wherein the CVD oxide layer is formed of a material selected from the group consisting of silicon oxide, aluminum oxide, zirconium oxide, and tantalum oxide.

4. (Currently amended) The method of claim 1, further comprising: forming ~~another~~
a material layer on the CVD oxide layer in the CVD apparatus.

5. (Previously presented) The method of claim 1, wherein growing a thermal oxide layer comprises using O₂, N₂O or a combination thereof for an oxidizing ambient.

6. (Original) The method of claim 1, wherein growing a thermal oxide layer is carried out at a temperature of approximately 750°C to 1000°C.

7. (Previously presented) The method of claim 1, wherein growing a thermal oxide layer is carried out at a temperature of approximately 750°C to 1000°C and forming a CVD oxide layer is carried out at a temperature of approximately 700°C to 850°C.

8. (Previously presented) The method of claim 1, wherein the surface of the semiconductor substrate comprises a bottom and a sidewall of a trench formed by etching the substrate to a predetermined depth; and

wherein the thermal oxide layer is formed to a thickness of approximately 20Å to 100Å, and the CVD oxide layer is formed to a thickness of approximately 50Å to 400Å.

9. (Previously presented) The method of claim 8, wherein the CVD oxide layer is formed of a material selected from the group consisting of silicon oxide, aluminum oxide, zirconium oxide, and tantalum oxide.

10. (Previously presented) The method of claim 8, wherein growing a thermal oxide layer uses O₂, N₂O or a combination thereof as a source gas at a temperature of approximately 750°C to 1000°C, and forming a CVD oxide layer is carried out using N₂O and SiH₄ as source gases at a temperature of approximately 700°C to 850°C.

11. (Previously presented) The method of claim 8, further comprising: forming a nitride liner layer on the CVD oxide layer in the CVD apparatus to a thickness of approximately 30Å to 100Å, and forming a trench filling layer on the nitride liner layer in the CVD apparatus to a thickness of approximately 3000Å to 10000Å.

12. (Currently amended) A method of forming [[an]]a composite oxide layer having a first thickness in an integrated circuit device, the method comprising:

forming a thermal oxide layer having a second thickness thinner than the first thickness on an exposed single crystalline silicon substrate in a chemical vapor deposition (CVD) apparatus; and

forming a CVD oxide layer~~[[,]]~~ directly on the thermal oxide layer in the CVD apparatus after forming the thermal oxide layer, the CVD oxide layer having a third thickness substantially equal to the differential thickness between the first thickness and the second thickness ~~directly on the thermal oxide layer in the same CVD apparatus,~~

wherein a thickness of approximately 8.8 Å to 44 Å of the exposed single crystalline silicon substrate is consumed during the forming of the thermal oxide layer.

13. (Previously presented) The method of claim 12, wherein forming a thermal oxide layer is carried out at a temperature of approximately 750°C to 1000°C, and forming a CVD oxide layer is carried out at a temperature of approximately 700°C to 850°C.

14. (Previously presented) The method of claim 13, wherein O₂, N₂O or combination thereof is used as a source gas for forming a thermal oxide layer, and N₂O and SiH₄ are used as a source gas for forming a CVD oxide layer.

15. (Currently amended) A method of forming ~~a layer for an~~ integrated circuit device, comprising:

forming a trench in a single crystalline silicon substrate by etching;

forming ~~[[an]]~~a composite oxide layer of a double layer structure with a first thickness on a surface of the trench;

forming a nitride liner layer on the composite oxide layer,

wherein forming the composite oxide layer comprises:

forming a thermal oxide layer having a second thickness of 20 Å to 100 Å on the trench;

forming a CVD conformal liner material layer directly on the thermal oxide layer, the CVD conformal liner material layer having a third thickness substantially equal to a difference between the first thickness and the second thickness ~~directly on the oxide layer~~,

wherein the thermal oxide layer, the CVD conformal liner material layer, and the nitride liner layer are formed in the same chemical vapor deposition (CVD) apparatus,

and wherein a thickness of 8.8 Å to 44 Å of the single crystalline silicon substrate is consumed during the forming of the thermal oxide layer.

16. (Cancelled)

17. (Currently amended) The method of claim 15, wherein the CVD conformal liner material layer is formed to a thickness of 50Å to 400Å.

18. (Currently amended) The method of claim 15, wherein the CVD conformal liner material layer is made of a material selected from the group consisting of silicon dioxide, aluminum trioxide, zirconium oxide, and tantalum pentoxide.

19. (Cancelled)

20. (Currently amended) The method of claim 15, wherein the thermal oxide layer is formed using O_2 , N_2O or a combination thereof as a source gas at a temperature of approximately $750^\circ C$ to $1000^\circ C$, and the CVD conformal liner material layer is a high temperature oxide layer formed using N_2O and SiH_4 as a source gas at a temperature of approximately $700^\circ C$ to $850^\circ C$.

21. (Original) The method of claim 20, further comprising: forming a trench isolation material on the nitride liner layer in the same CVD apparatus to fill the trench.

22. (Currently amended) A method of forming an isolation trench, comprising:
etching a single crystalline silicon substrate to form a trench therein;
forming ~~[[an]]~~a composite oxide layer having a double layer structure with a first thickness on a surface of the trench;
forming a nitride liner layer on the composite oxide layer; and~~[[.]]~~
forming a trench isolation material layer on the nitride liner layer to fill the trench, wherein forming the composite oxide layer comprises:
forming a thermal oxide layer having a second thickness of 20 \AA to 100 \AA on the trench;
forming a CVD conformal liner material layer directly on the thermal oxide layer, the CVD conformal liner material layer having a third thickness substantially equal to a difference between the first thickness and the second thickness~~directly on the oxide layer~~,
wherein the thermal oxide layer, the CVD conformal liner material layer, and the nitride liner layer, and the trench isolation layer are formed in the same chemical vapor deposition (CVD) apparatus,
and wherein a thickness of 8.8 \AA to 44 \AA of the single crystalline silicon substrate is consumed during the forming of the thermal oxide layer.

23. (Cancelled)

24. (Currently amended) The method of claim 22, wherein the CVD conformal liner material layer is formed to a thickness of 50Å to 400Å.

25. (Currently amended) The method of claim 22, wherein the thermal oxide layer is formed using O₂, N₂O or a combination thereof as a source gas at a temperature of approximately 750°C to 1000°C, and the CVD conformal liner material layer is a higher temperature oxide layer formed using N₂O and SiH₄ as a source gas at a temperature of approximately 700°C to 850°C.

26. (Currently amended) The method of claim 22, wherein the CVD conformal liner material layer is made of a material selected from the group consisting of silicon oxide, aluminum oxide, zirconium oxide, and tantalum oxide.

27. (Cancelled)

28. (Cancelled)